

JMTQ080P03A

Features

- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% V_{DS} Tested
- Halogen-free; RoHS-compliant
- Pb-free plating

Applications

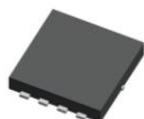
- Load Switch
- PWM Application
- Power Management

Product Summary

Parameters	Value	Unit
V_{DSS}	-30	V
$V_{GS(th_Typ)}$	-1.5	V
$I_D(@V_{GS}=-10V)$	-50	A
$R_{DS(ON_Typ)}(@V_{GS}=-10V)$	5.9	mΩ
$R_{DS(ON_Typ)}(@V_{GS}=-4.5V)$	8.1	mΩ



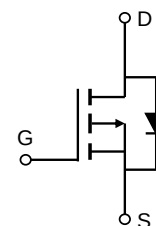
Top View



Bottom View



Pin Assignment



Schematic

PDFN3X3-8L

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMTQ080P03A	Q080P03A	1	Tape&Reel	PDFN3x3-8L	5000	50000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	-30	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	A
		$T_C = 100^\circ\text{C}$	
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	133	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	W
		$T_C = 100^\circ\text{C}$	
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max	Unit
R	Thermal Resistance, Junction to Ambient ⁽³⁾	41	$^\circ\text{C/W}$
R	Thermal Resistance, Junction to Case	4.2	

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = -250μA, V _{GS} = 0V	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} = 0V	-	-	-1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-1.1	-1.5	-2.0	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = -10V, I _D = -20A	-	5.9	7.4	mΩ
		V _{GS} = -4.5V, I _D = -10A	-	8.1	10.1	mΩ
Dynamic Characteristics						
R _g	Gate Resistance	f = 1MHz	-	11.5	-	Ω
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = -15V, f = 1MHz	2405	3366	4545	pF
C _{oss}	Output Capacitance		336	471	635	pF
C _{rss}	Reverse Transfer Capacitance		232	324	438	pF
Q _g	Total Gate Charge	V _{GS} = 0 to -10V V _{DS} = -15V, I _D = -10A	-	59	-	nC
Q _{gs}	Gate Source Charge		-	9.5	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	14	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = -10V, V _{DD} = -15V I _D = -10A, R _{GEN} = 2.7Ω	-	6.8	-	ns
t _r	Turn-On Rise Time		-	5.7	-	ns
t _{d(off)}	Turn-Off DelayTime		-	112	-	ns
t _f	Turn-Off Fall Time		-	78	-	ns
Body Diode Characteristics						
I _S	Maximum Continuous Body Diode Forward Current		-	-	-50	A
I _{SM}	Maximum Pulsed Body Diode Forward Current		-	-	-202	A
V _{SD}	Body Diode Forward Voltage	V _{GS} = 0V, I _S = -20A	-		-1.2	V
trr	Body Diode Reverse Recovery Time	I _F = -10A, di/dt = 100A/us	15	21	29	ns
Qrr	Body Diode Reverse Recovery Charge		-	9.8	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = -15\text{V}$, $V_{GS} = -10\text{V}$, $R_G = 25\text{ohm}$, $L = 0.5\text{mH}$, $I_{AS} = -23.1\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
3. R is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
4. Pulse Test: Pulse Width $\leq$ $\leq 0.5\%$.



Typical Performance Characteristics

Figure 1: Power De-rating

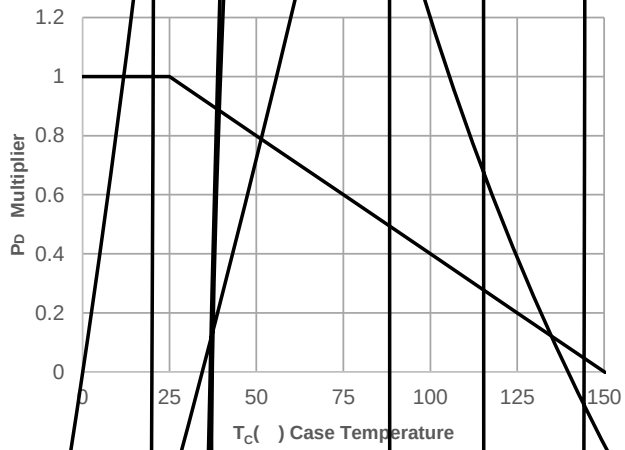
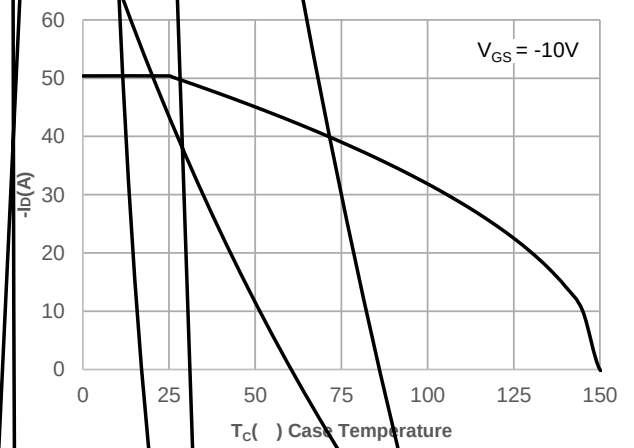
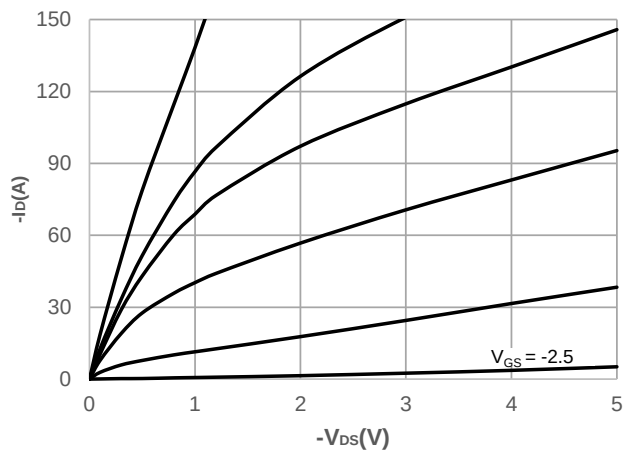


Figure 2: Current De-rating



Typical Performance Characteristics

Figure 5: Output Characteristics



Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

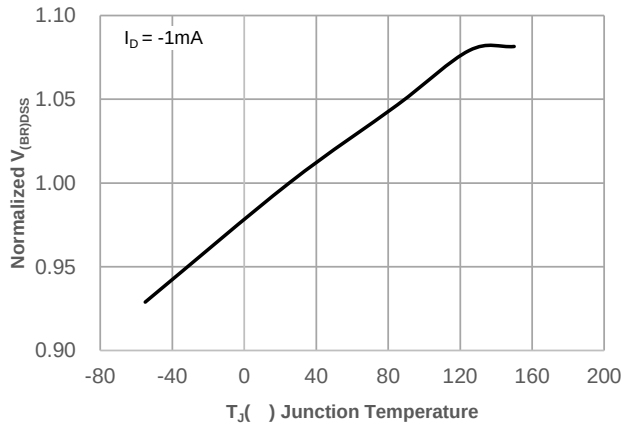


Figure 12: Normalized on Resistance vs. Junction Temperature

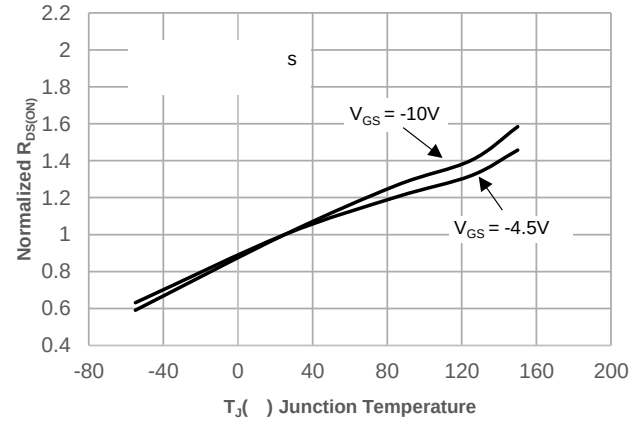


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

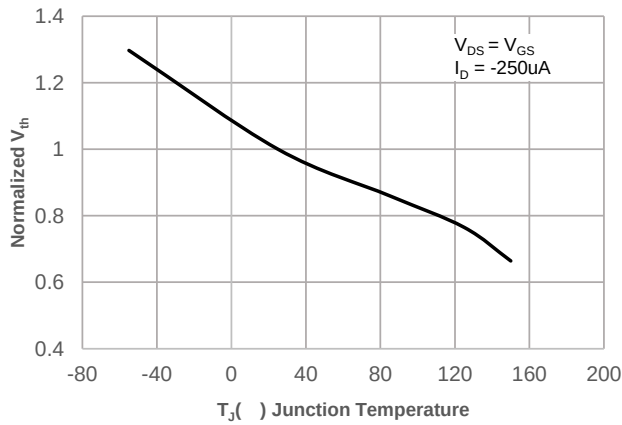


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

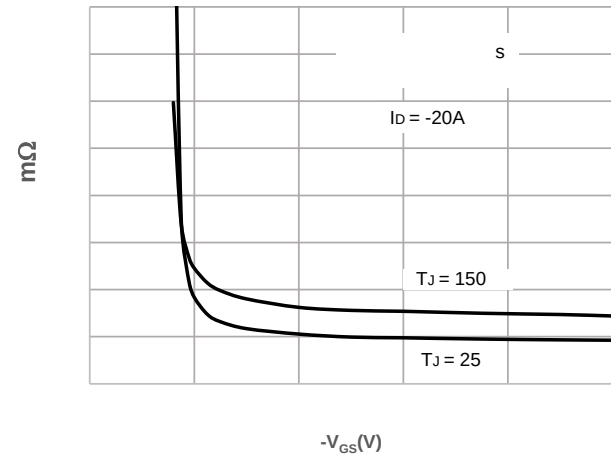
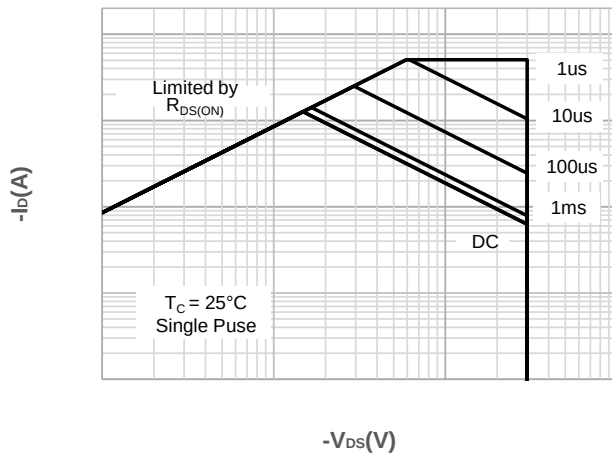


Figure 15: Maximum Safe Operating Area



Test Circuit

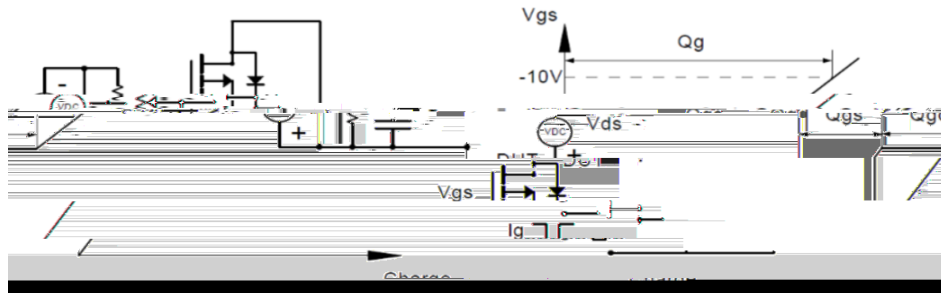


Figure 1: Gate Charge Test Circuit & Waveform

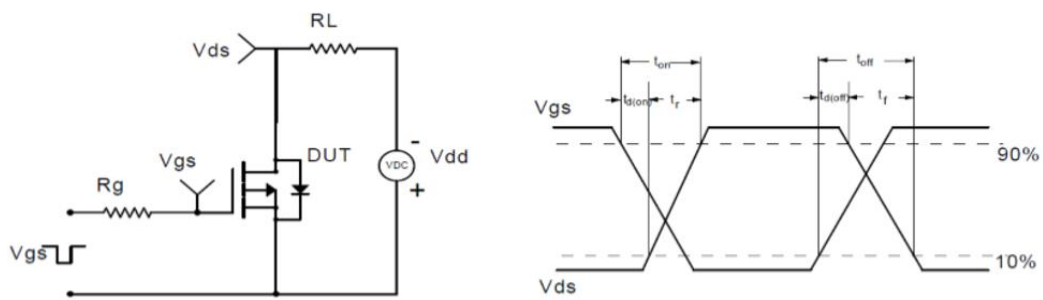


Figure 2: Resistive Switching Test Circuit & Waveform

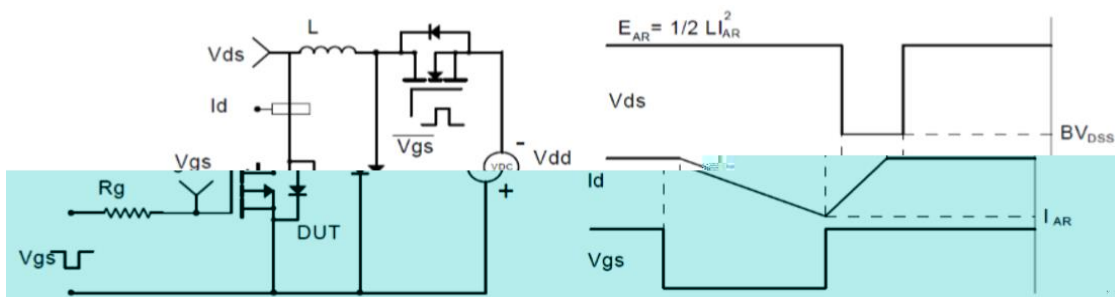


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

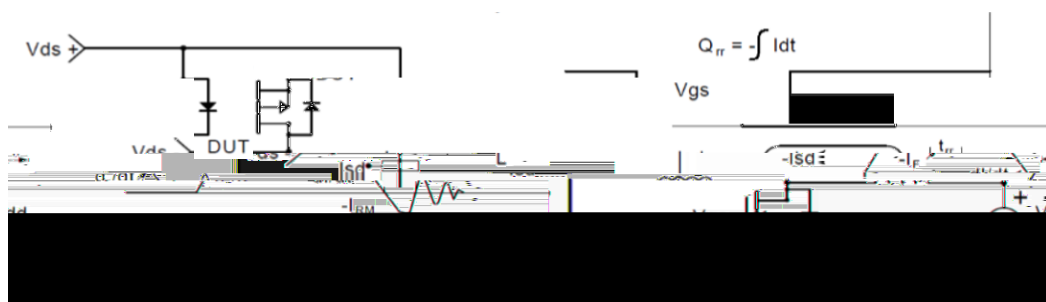
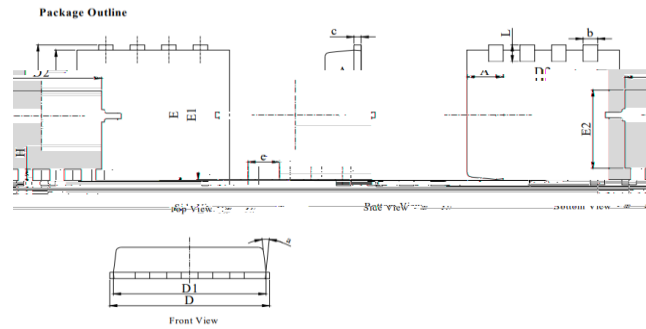


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PDFN3x3-8L)

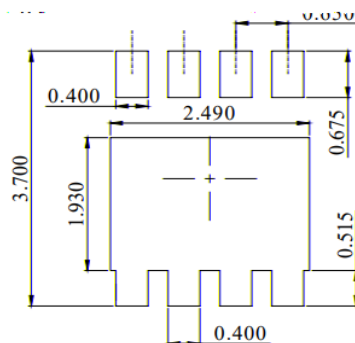


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMNESIONS IN MILLIMETER (ANNGLE IN DEGREE).

MAX.	MIN.	NOM.
0.80	0.70	0.75
0.35	0.25	0.30
0.25	0.10	0.20
3.25	3.00	3.15
3.15	2.95	3.05
2.59	2.39	2.49
2.30	2.10	2.20
1.85	1.65	1.75
1.45	1.25	1.35
1.05	0.85	0.95
0.65	0.45	0.55
0.25	0.15	0.20
0.15	0.05	0.10
0.05	0.02	0.03

Recommended Soldering Footprint



DIMENSIONS:MILLIMETERS

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